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ON Semiconductor®

# FQD2N90 / FQU2N90

## N-Channel QFET® MOSFET

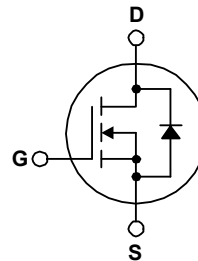
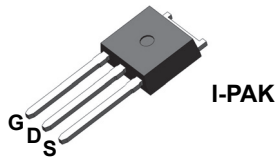
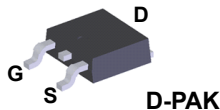
900 V, 1.7 A, 7.2 Ω

### Description

This N-Channel enhancement mode power MOSFET is produced using ON Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

### Features

- 1.7 A, 900 V,  $R_{DS(on)} = 7.2 \Omega$  (Max.) @  $V_{GS} = 10 V$ ,  $I_D = 0.85 A$
- Low Gate Charge (Typ. 12 nC)
- Low Crss (Typ. 5.5 pF)
- 100% Avalanche Tested
- RoHS Compliant



### Absolute Maximum Ratings $T_C = 25^\circ C$ unless otherwise noted.

Symbol	Parameter	FQD2N90TM FQU2N90TU-WS FQU2N90TU-AM002	Unit
$V_{DSS}$	Drain-Source Voltage	900	V
$I_D$	Drain Current - Continuous ( $T_C = 25^\circ C$ )	1.7	A
	- Continuous ( $T_C = 100^\circ C$ )	1.08	A
$I_{DM}$	Drain Current - Pulsed (Note 1)	6.8	A
$V_{GSS}$	Gate-Source Voltage	$\pm 30$	V
$E_{AS}$	Single Pulsed Avalanche Energy (Note 2)	170	mJ
$I_{AR}$	Avalanche Current (Note 1)	1.7	A
$E_{AR}$	Repetitive Avalanche Energy (Note 1)	5.0	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.0	V/ns
$P_D$	Power Dissipation ( $T_A = 25^\circ C$ ) *	2.5	W
	Power Dissipation ( $T_C = 25^\circ C$ )	50	W
	- Derate above $25^\circ C$	0.4	W/ $^\circ C$
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +150	$^\circ C$
$T_L$	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	$^\circ C$

### Thermal Characteristics

Symbol	Parameter	FQD2N90TM FQU2N90TU-WS FQU2N90TU-AM002	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	2.5	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (minimum pad of 2 oz copper), Max.	110	
	Thermal Resistance, Junction to Ambient (*1 in <sup>2</sup> pad of 2 oz copper), Max.	50	

FQD2N90 / FQU2N90 — N-Channel QFET® MOSFET

## Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQD2N90TM	FQD2N90	D-PAK	Tape and Reel	330 mm	16 mm	2500 units
FQU2N90TU-WS	FQU2N90S	I-PAK	Tube	N/A	N/A	75 units
FQU2N90TU-AM002	FQU2N90	I-PAK	Tube	N/A	N/A	75 units

## Electrical Characteristics $T_c = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
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### Off Characteristics

$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	900	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$	--	1.0	--	$\text{V}/^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 900\text{ V}, V_{GS} = 0\text{ V}$	--	--	10	$\mu\text{A}$
		$V_{DS} = 720\text{ V}, T_C = 125^\circ\text{C}$	--	--	100	$\mu\text{A}$
$I_{GSSF}$	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
$I_{GSSR}$	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

### On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	3.0	--	5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 0.85\text{ A}$	--	5.6	7.2	$\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 50\text{ V}, I_D = 0.85\text{ A}$	--	1.7	--	S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	390	500	pF
$C_{oss}$	Output Capacitance		--	45	60	pF
$C_{rss}$	Reverse Transfer Capacitance		--	5.5	7.0	pF

### Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 450\text{ V}, I_D = 2.2\text{ A},$ $R_G = 25\ \Omega$	--	15	40	ns
$t_r$	Turn-On Rise Time		--	35	80	ns
$t_{d(off)}$	Turn-Off Delay Time		--	20	50	ns
$t_f$	Turn-Off Fall Time		(Note 4)	--	30	70
$Q_g$	Total Gate Charge	$V_{DS} = 720\text{ V}, I_D = 2.2\text{ A},$ $V_{GS} = 10\text{ V}$	--	12	15	nC
$Q_{gs}$	Gate-Source Charge		--	2.8	--	nC
$Q_{gd}$	Gate-Drain Charge		(Note 4)	--	6.1	--

### Drain-Source Diode Characteristics and Maximum Ratings

$I_S$	Maximum Continuous Drain-Source Diode Forward Current	--	--	1.7	A	
$I_{SM}$	Maximum Pulsed Drain-Source Diode Forward Current	--	--	6.8	A	
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 1.7\text{ A}$	--	--	1.4	V
$t_{rr}$	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 2.2\text{ A},$	--	400	--	ns
$Q_{rr}$	Reverse Recovery Charge	$dI_F / dt = 100\text{ A}/\mu\text{s}$	--	1.6	--	$\mu\text{C}$

#### Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2.  $L = 111\text{ mH}, I_{AS} = 1.7\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\ \Omega,$  Starting  $T_J = 25^\circ\text{C}$
3.  $I_{SD} \leq 2.2\text{ A}, di/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS},$  Starting  $T_J = 25^\circ\text{C}$
4. Essentially independent of operating temperature

## Typical Characteristics

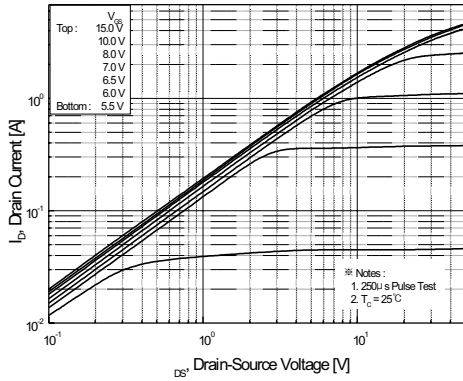


Figure 1. On-Region Characteristics

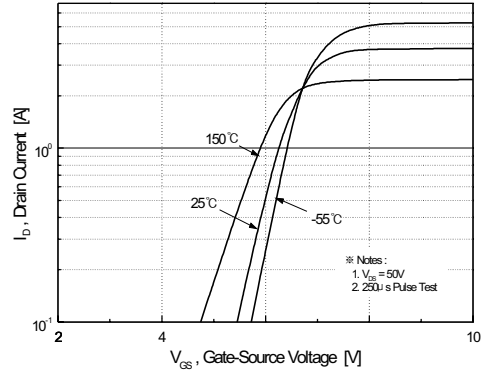


Figure 2. Transfer Characteristics

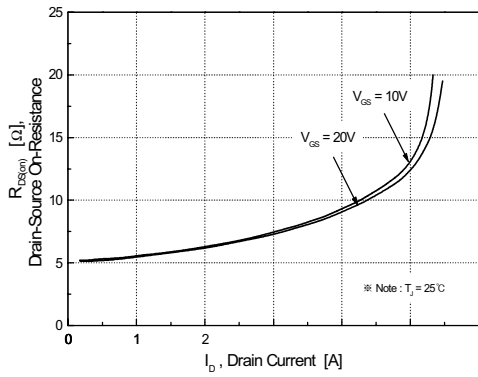


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

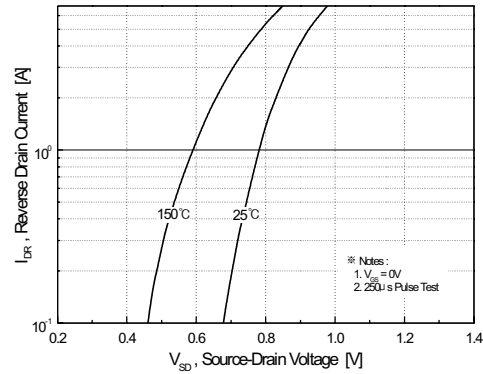


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

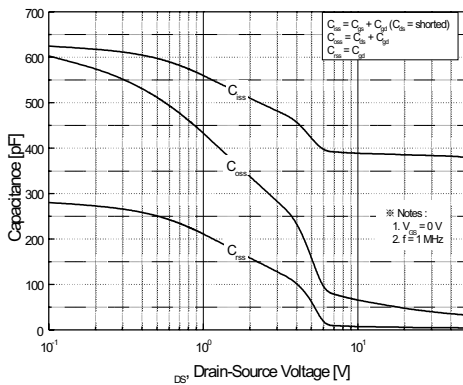


Figure 5. Capacitance Characteristics

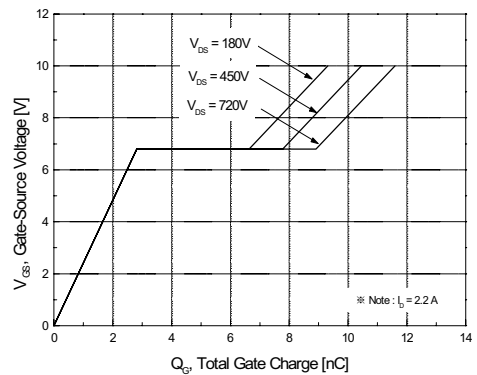
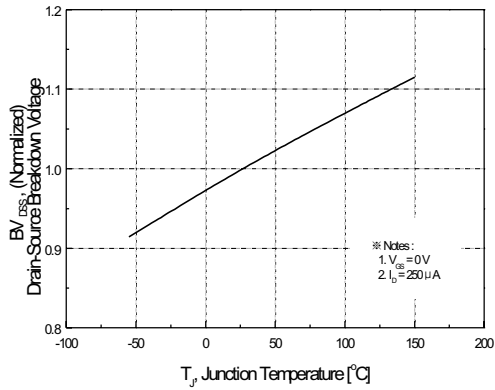
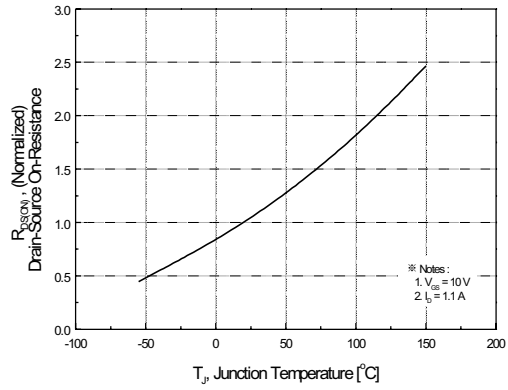


Figure 6. Gate Charge Characteristics

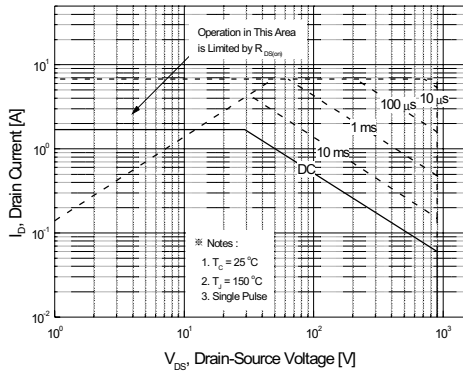
**Typical Characteristics** (Continued)



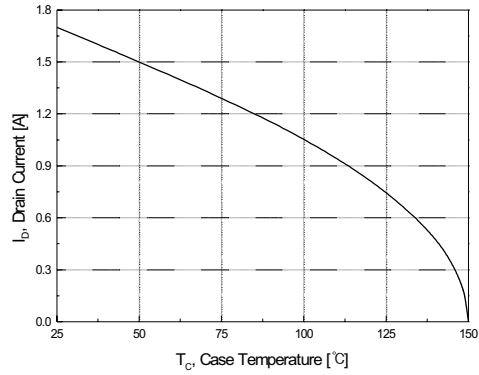
**Figure 7. Breakdown Voltage Variation vs. Temperature**



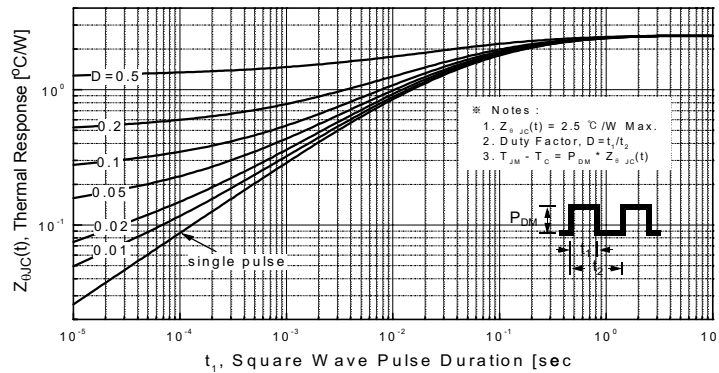
**Figure 8. On-Resistance Variation vs. Temperature**



**Figure 9. Maximum Safe Operating Area**



**Figure 10. Maximum Drain Current vs. Case Temperature**



**Figure 11. Transient Thermal Response Curve**

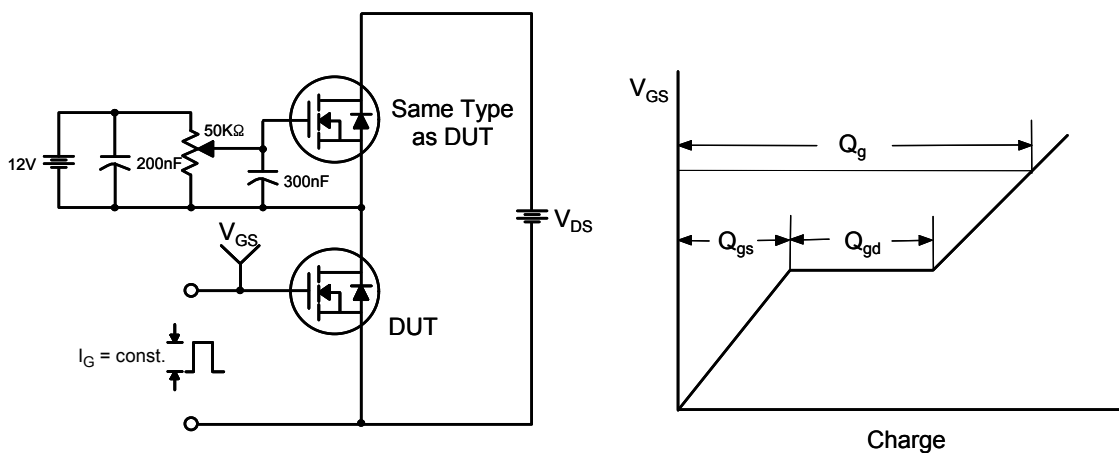


Figure 12. Gate Charge Test Circuit & Waveform

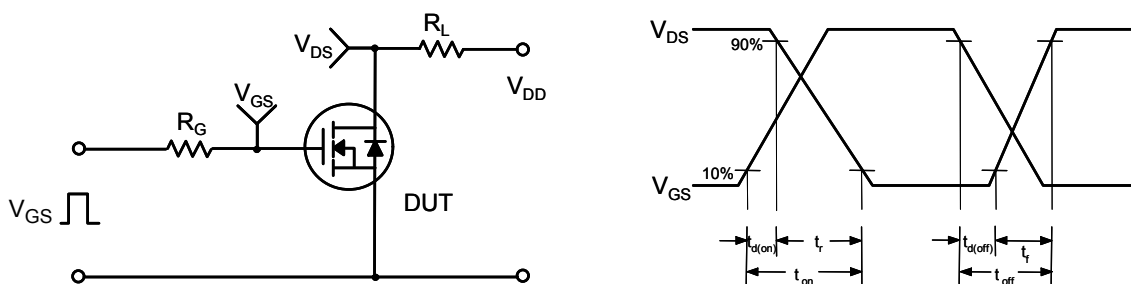


Figure 13. Resistive Switching Test Circuit & Waveforms

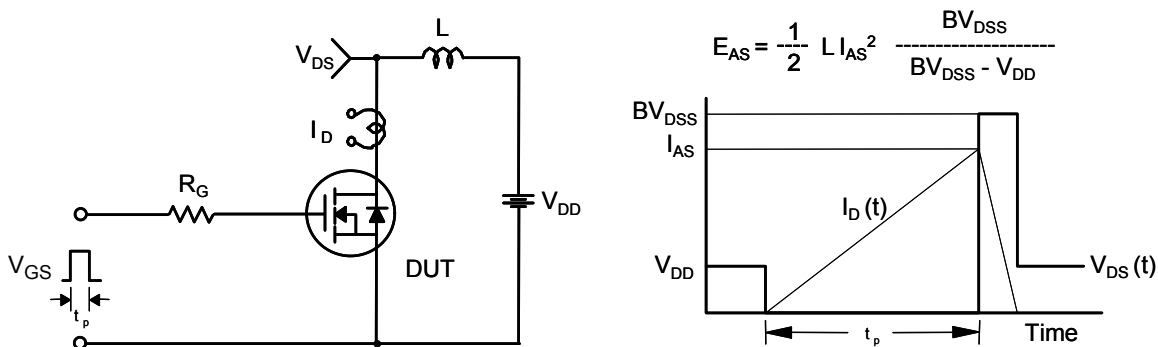


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

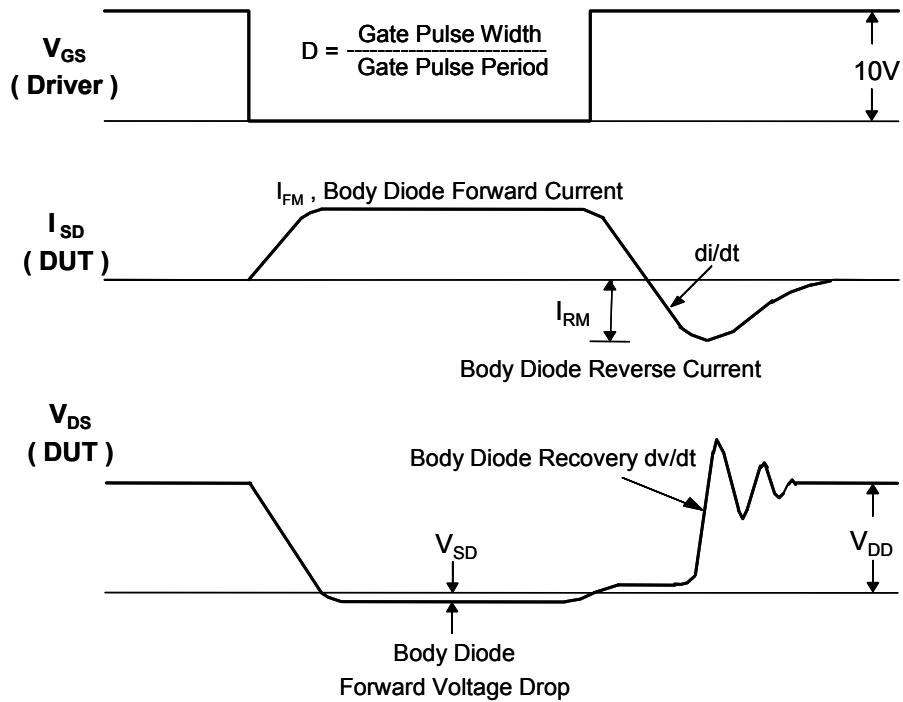
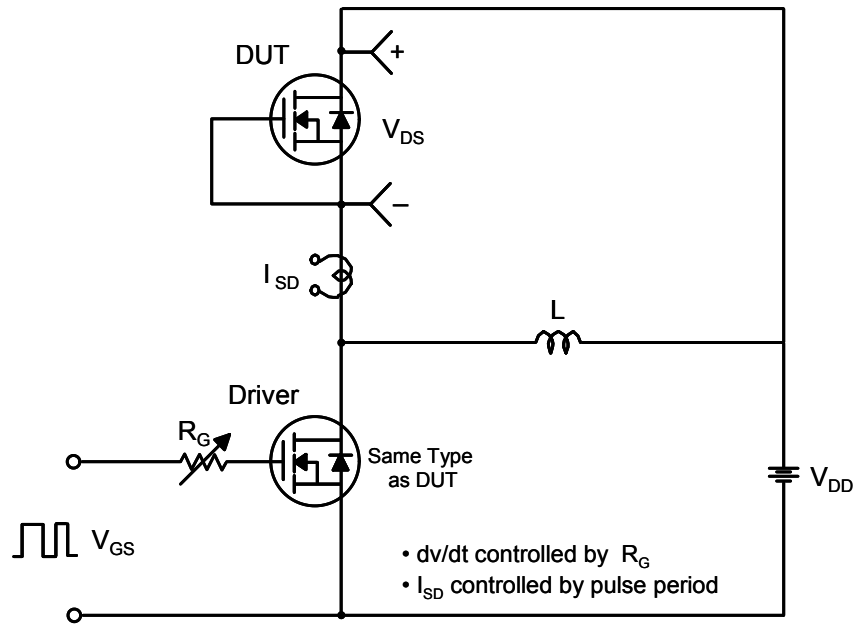
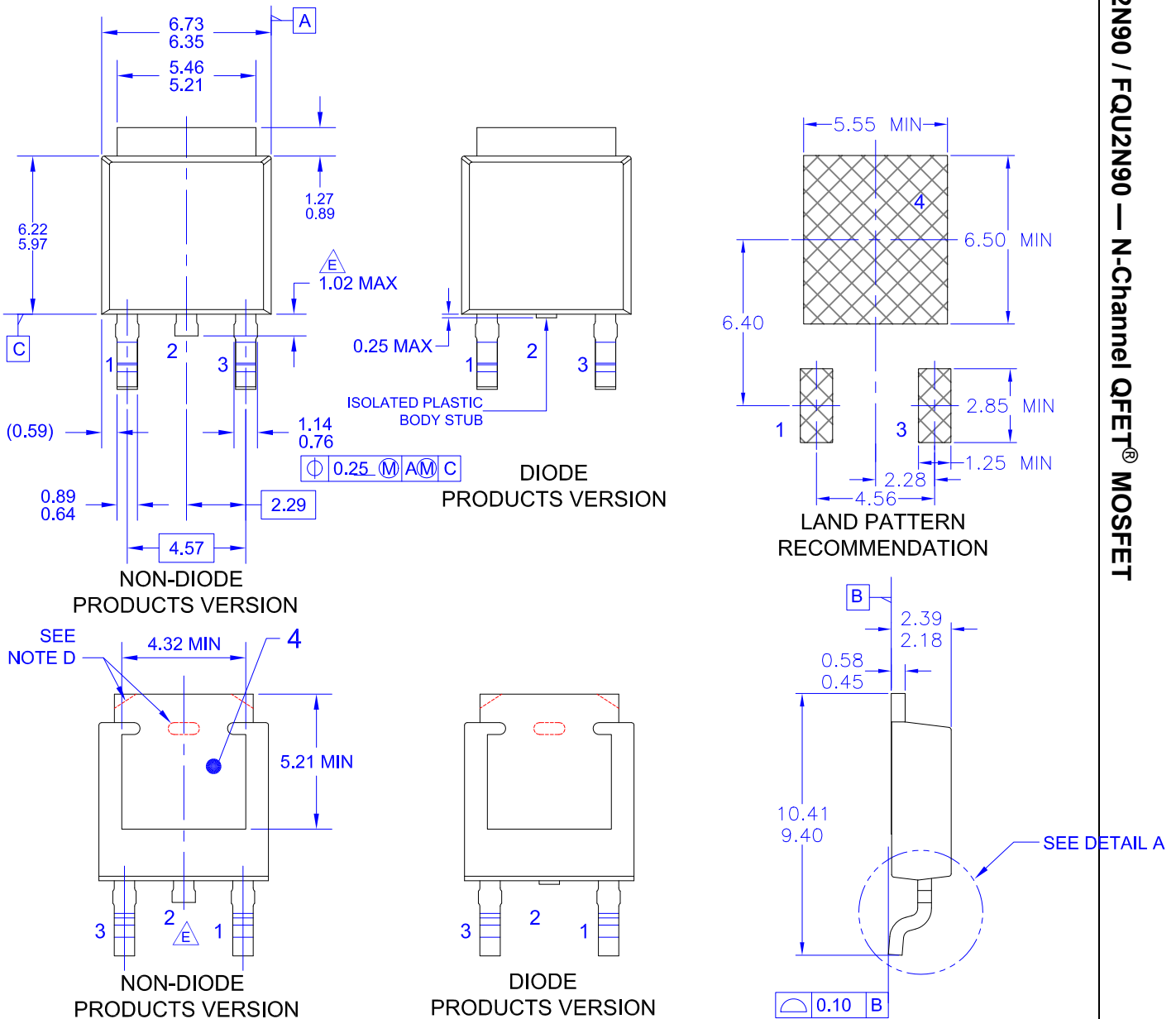


Figure 15. Peak Diode Recovery  $dv/dt$  Test Circuit & Waveforms

### Mechanical Dimensions

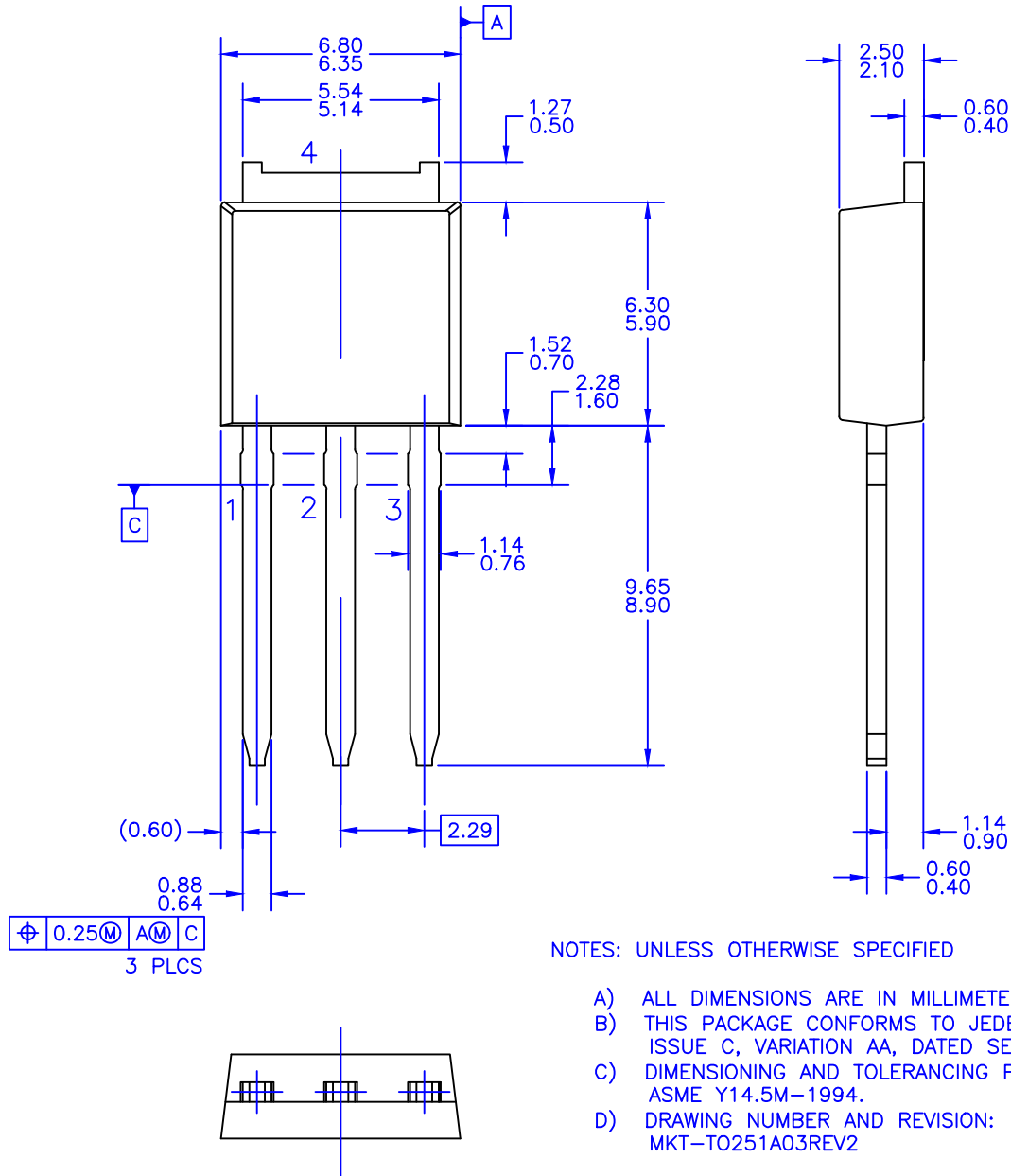


**NOTES: UNLESS OTHERWISE SPECIFIED**

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- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
- D) SUPPLIER DEPENDENT MOLD LOCKING HOLES OR CHAMFERED CORNERS OR EDGE PROTRUSION.
- E) TRIMMED METAL CENTER LEAD IS PRESENT ON FOR NON-DIODE PRODUCTS
- F) DIMENSIONS ARE EXCLUSIVE OF BURS, MOLD FLASH AND TIE BAR EXTRUSIONS.
- G) LAND PATTERN RECOMMENDATION IS BASED ON IPC7351A STD TO228P991X239-3N.
- H) DRAWING NUMBER AND REVISION: MKT-TO252A03REV11



## Mechanical Dimensions



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